

DAS-PM2S9B

P-Type Mono Cell

Product Feature

- ◇ Light Induced Degradation $\leq 2.5\%$
- ◇ PID resistant
- ◇ Power temperature coefficient $\leq -0.38\%/^{\circ}\text{C}$
- ◇ Relative conversion efficiency ($200\text{W}/\text{m}^2$) $\geq 95\%$
- ◇ Lower CTM loss, better for the high efficiency module

Quality Control

- ◇ The accuracy of the efficiency test is controlled at $\pm 0.1\%$
- ◇ IV/EL/Appearance 100% automatic inspection
- ◇ Calibration Cell source to Fraunhofer ISE

Management System Certification

- ◇ ISO 9001:2015 Quality Management System
- ◇ ISO 14001:2015 Environmental Management System
- ◇ ISO 45001:2018 Occupational Health and Safety Management System

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Product Features

Dimension:	156.75mmx156.75mm±0.25mm, Φ210.0mm±0.25mm
Cell Thickness:	180μm±20μm
Front side:	0.06±0.01mm wide bus bars, 110 finger grids, SiN
Back side:	1.67±0.1 mm wide discontinuous soldering pads, Aluminum back surface field

Temperature Coefficients

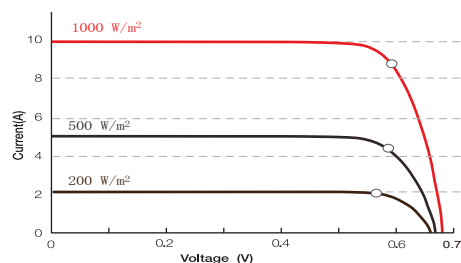
Current Temperature Coefficient	Tkcurrent: +0.048 %/K
Voltage Temperature Coefficient	Tkvoltage: -0.31 %/K
Power Temperature Coefficient	Tkpower: -0.38 %/K

Electric Performance

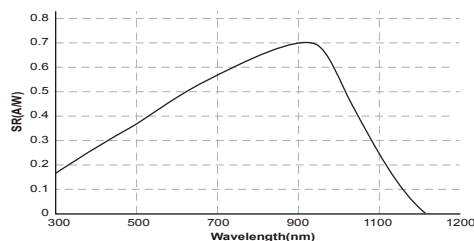
Eff(%)	Pmpp(W)	Ump(V)	Imp(A)	Uoc(V)	Isc(A)	FF(%)
22.40%	5.47	0.575	9.421	0.677	9.940	81.49
22.30%	5.45	0.576	9.481	0.676	9.929	81.36
22.20%	5.42	0.575	9.457	0.675	9.919	81.22
22.10%	5.40	0.574	9.435	0.674	9.903	81.14
22.00%	5.38	0.573	9.411	0.673	9.889	81.03
21.90%	5.35	0.572	9.383	0.672	9.870	80.92
21.80%	5.33	0.571	9.372	0.671	9.865	80.83
21.70%	5.30	0.569	9.364	0.670	9.844	80.76
21.60%	5.28	0.567	9.343	0.669	9.830	80.60
21.50%	5.25	0.565	9.319	0.668	9.806	80.44
21.40%	5.23	0.564	9.291	0.667	9.787	80.26
21.30%	5.20	0.563	9.261	0.666	9.771	80.09

- Standard Test Conditions: 1000W/ m², AM 1.5, 25°C
- Specifications and data are only for reference.

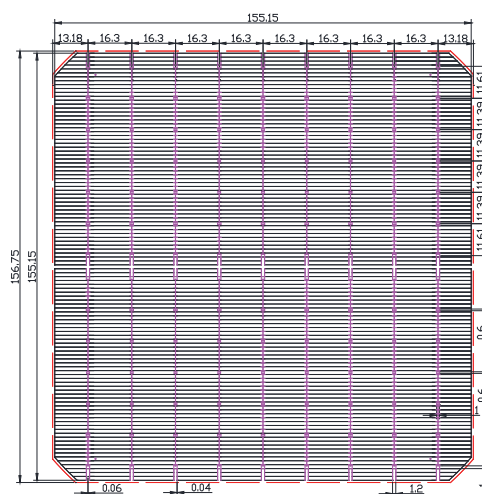
IV Curve



Spectral Response (SR)



Front side



Rear side

